MT6L56E



Preliminary

TOSHIBA Transistor Silicon NPN Epitaxial Planar Type

MT6L56E

VHF-UHF Band Low Noise Amplifier Application VHF-UHF Band Oscillator Application

• Two devices are built into the super-thin and ultra-super-mini (6-pin) ES6 package.

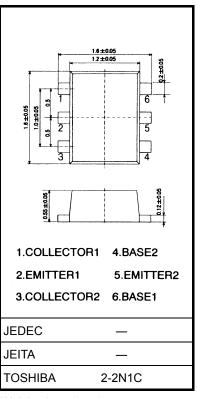
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Mounted Devices

	Q1: SSM (TESM)	Q2: TESM
Three-pin (SSM/TESM) product No.	MT3S07S (MT3S07T)	MT3S08T

Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Q1	Q2	Unit		
Collector-base voltage	V _{CBO}	10	20	V		
Collector-emitter voltage	V _{CEO}	5	8	V		
Emitter-base voltage	V _{EBO}	1.5	1.5	V		
Collector current	Ι _C	25	40	mA		
Base current	Ι _Β	7	10	mA		
Collector power dissipation	P _C (Note 1)	150		mW		
Junction temperature	Tj	125		125		°C
Storage temperature range	T _{stg}	-55~125		-55~125		°C



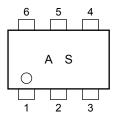
Weight: 3 mg (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

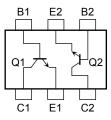
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Total power dissipation of Q1 and Q2 mounted on the circuit board

Marking



Pin Connections



Unit: mm

Electrical Characteristics Q1-Side (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	$V_{CB} = 5 \text{ V}, \text{ I}_{E} = 0$	—	_	0.1	μA
Emitter cut-off current	I _{EBO}	$V_{EB} = 1 \text{ V}, \text{ I}_{C} = 0$	—	_	1	μA
DC current gain	h _{FE}	$V_{CE} = 1 \text{ V}, \text{ I}_{C} = 5 \text{ mA}$	70	_	140	—
Transition frequency	f _T	$V_{CE} = 3 \text{ V}, \text{ I}_{C} = 10 \text{ mA}$	10	12	—	GHz
Insertion gain	S _{21e} ² (1)	$V_{CE} = 1 \text{ V}, \text{ I}_{C} = 5 \text{ mA}, \text{ f} = 2 \text{ GHz}$	—	6.5	_	dB
	S _{21e} ² (2)	$V_{CE} = 3 \text{ V}, \text{ I}_{C} = 15 \text{ mA}, \text{ f} = 2 \text{ GHz}$	4	7	_	
Noise figure	NF (1)	$V_{CE} = 1 \text{ V}, I_C = 5 \text{ mA}, f = 2 \text{ GHz}$	—	1.6	3	dB
	NF (2)	$V_{CE} = 3 \text{ V}, \text{ I}_{C} = 5 \text{ mA}, \text{ f} = 2 \text{ GHz}$	—	1.5	3	
Reverse transfer capacitance	C _{re}	$V_{CB} = 1 \text{ V}, \text{ I}_{E} = 0, \text{ f} = 1 \text{ MHz} \qquad (\text{Note } 2$) —	0.45	0.85	pF

Electrical Characteristics Q2-Side (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	$V_{CB} = 10 \text{ V}, \text{ I}_{E} = 0$	—	_	0.1	μA
Emitter cut-off current	I _{EBO}	$V_{EB} = 1 V, I_{C} = 0$	—		1	μA
DC current gain	h _{FE}	$V_{CE} = 1 V, I_{C} = 5 mA$	80	_	140	—
Transition frequency	fT	$V_{CE} = 1 \text{ V}, \text{ I}_{C} = 5 \text{ mA}$	2	4.5	_	GHz
Insertion gain	S _{21e} ² (1)	$V_{CE} = 1 \text{ V}, \text{ I}_{C} = 5 \text{ mA}, \text{ f} = 1 \text{ GHz}$	_	9.5	_	dB
	S _{21e} ² (2)	$V_{CE} = 3 V, I_C = 20 mA, f = 1 GHz$	9.5	12.5	_	
Noise figure	NF	$V_{CE} = 1 \text{ V}, \text{ I}_{C} = 5 \text{ mA}, \text{ f} = 1 \text{ GHz}$	_	1.4	2.5	dB
Reverse transfer capacitance	C _{re}	$V_{CB} = 1 \text{ V}, \text{ I}_{E} = 0, \text{ f} = 1 \text{ MHz}$ (Note 2)	_	0.55	0.95	pF

Note 2: C_{re} is measured by 3 terminal method with capacitance bridge.

Handling Precaution

When handling individual devices (which are not yet mounted on a circuit board), be sure that the environment is protected against electrostatic electricity. Operators should wear anti-static clothing, and containers and other objects that come into direct contact with devices should be made of anti-static materials.

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